Unit: mm

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

# **TLP185**

Office Machine

**Programmable Controllers** 

**AC Adapter** 

I/O Interface Board

The TOSHIBA mini flat coupler TLP185 is a small outline coupler, suitable for surface mount assembly.

TLP185 consist of a photo transistor optically coupled to a gallium arsenide infrared emitting diode. Since TLP185 is smaller than DIP package, it's suitable for high-density surface mounting applications such as programmable controllers

• Collector-emitter voltage: 80V (min)

• Current transfer ratio: 50% (min)

Rank GB: 100% (min)

• Isolation voltage: 3750Vrms (min)

• Operation Temperature:-55 to 110 °C

Safety Standards

UL approved: UL1577, File No. E67349

cUL approved: CSA Component Acceptance Service No. 5A

File No.E67349

BSI approved: BS EN60065:2002, Certificate No. 9020

BS EN60950-1:2006, Certificate No. 9021

• Option (V4) type

VDE approved: EN60747-5-2, Certificate No. 40009347 (Note): When a EN60747-5-2 approved type is needed,

Please designate "Option(V4)"

Construction mechanical rating

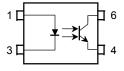
Creepage distance : 5.0 mm(min)
Clearance : 5.0 mm(min)
Insulation thickness : 0.4 mm(min)

11-4M1S

Weight: 0.08 g (Typ.)

**TOSHIBA** 

## Pin Configuration(top view)



- 1: Anode
- 3: Cathode
- 4: Emitter
- 6: Collector

## **Current Transfer Ratio**

			sfer Ratio (%) / I <sub>F</sub> )	Marking Of Classification		
Туре	Classification Note1	I <sub>F</sub> = 5mA, V <sub>CE</sub> :	= 5V, Ta = 25°C			
		Min	Max			
	Blank	50	400	Blank, YE, GR, GB, Y+, G, G+, B		
	Rank Y	50	150	YE		
	Rank GR	100	300	GR		
TLP185	Rank GB	100	400	GB		
111100	Rank YH	75	150	Y+		
	Rank GRL	100	200	G		
	Rank GRH	150	300	G+		
	Rank BLL	200	400	В		

(Note1): Ex Rank GB: TLP185 (GB,E

(Note) Application, type name for certification test, please use standard product type name, i, e. TLP185(GB,E:TLP185

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## Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
	Forward current	IF	50	mA
	Forward current derating (Ta ≥ 90°C)	ΔI <sub>F</sub> / °C	-1.5	mA / °C
ED	Pulse forward current (Note2)	I <sub>FP</sub>	1	Α
	Reverse voltage	V <sub>R</sub>	5	V
	Junction temperature	Tj	125	°C
	Collector-emitter voltage	V <sub>CEO</sub>	80	V
	Emitter-collector voltage	V <sub>ECO</sub>	7	V
Detector	Collector current	IC	50	mA
Dete	Collector power dissipation	PC	150	mW
	Collector power dissipation derating (Ta ≥ 25°C)	ΔP <sub>C</sub> / °C	-1.5	mW / °C
	Junction temperature	Tj	125	°C
Оре	erating temperature range	T <sub>opr</sub>	−55 to 110	°C
Stor	rage temperature range	T <sub>stg</sub>	−55 to 125	°C
Lea	d soldering temperature	T <sub>sol</sub>	260 (10s)	°C
Total package power dissipation		P <sub>T</sub>	200	mW
Tota	al package power dissipation derating (Ta ≥ 25°C)	ΔP <sub>T</sub> / °C	P <sub>T</sub> / °C -2.0	
Isola	ation voltage (AC, 1min., R.H. ≤ 60%) (Note 3)	BVS	3750	V <sub>rms</sub>

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Pulse width ≤ 100 µs,f=100 Hz

Note 3: Device considered a two terminal device: Pins 1 and 3 shorted together and 4 and 6 shorted together.

## **Recommended Operating Conditions (Note)**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>CC</sub>	_	5	48	V
Forward current	lF	_	16	20	mA
Collector current	IC	_	1	10	mA

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

# Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
	Forward voltage	$V_{F}$	I <sub>F</sub> = 10 mA	1.1	1.25	1.4	V
LED	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	5	μА
	Capacitance	C <sub>T</sub>	V = 0, f = 1 MHz	_	30	_	pF
	Collector-emitter breakdown voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> = 0.5 mA	80	_	1	٧
Detector	Emitter-collector breakdown voltage	V <sub>(BR)</sub> ECO	I <sub>E</sub> = 0.1 mA	7	ı	ı	V
Dete	Collector dark current I <sub>CEO</sub>	loso	V <sub>CE</sub> = 48 V		0.01	0.08	μΑ
		ICEO	V <sub>CE</sub> = 48 V, Ta = 85°C	_	2	50	μΑ
	Capacitance (collector to emitter)	C <sub>CE</sub>	V = 0, f = 1 MHz		10		pF

# **Coupled Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	MIn	Тур.	Max	Unit
Current transfer ratio	I <sub>C</sub> / I <sub>F</sub>	I <sub>F</sub> = 5 mA, V <sub>CE</sub> = 5 V	50	_	400	- %
Current transfer ratio	1C / 1F	Rank GB	100	_	400	
Saturated CTR	I <sub>C</sub> / I <sub>F (sat)</sub>	IF = 1 mA, V <sub>CE</sub> = 0.4 V Rank GB	_	60	_	- %
Saturated CTK			30	_	_	
		I <sub>C</sub> = 2.4 mA, I <sub>F</sub> = 8 mA	_	_	0.3	
Collector-emitter saturation voltage	VCE (sat)	I <sub>C</sub> = 0.2 mA, I <sub>F</sub> = 1 mA Rank GB	_	0.2	_	V
ğ			_	_	0.3	
Off-state collector current	I <sub>C (off)</sub>	V <sub>F</sub> = 0.7V, V <sub>CE</sub> = 48 V	_	1	10	μΑ

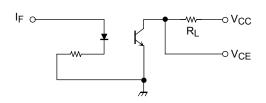
## **Isolation Characteristics (Ta = 25°C)**

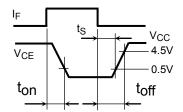
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance (input to output)	CS	V <sub>S</sub> = 0V, f = 1 MHz	-	8.0	-	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H. ≤ 60%	1×10 <sup>12</sup>	10 <sup>14</sup>	_	Ω
	BV <sub>S</sub>	AC, 1 minute	3750	-	_	- V <sub>rms</sub>
Isolation voltage		AC, 1 second, in oil	_	10000	-	
		DC, 1 minute, in oil	_	10000	_	V <sub>dc</sub>

# Switching Characteristics (Ta = 25°C)

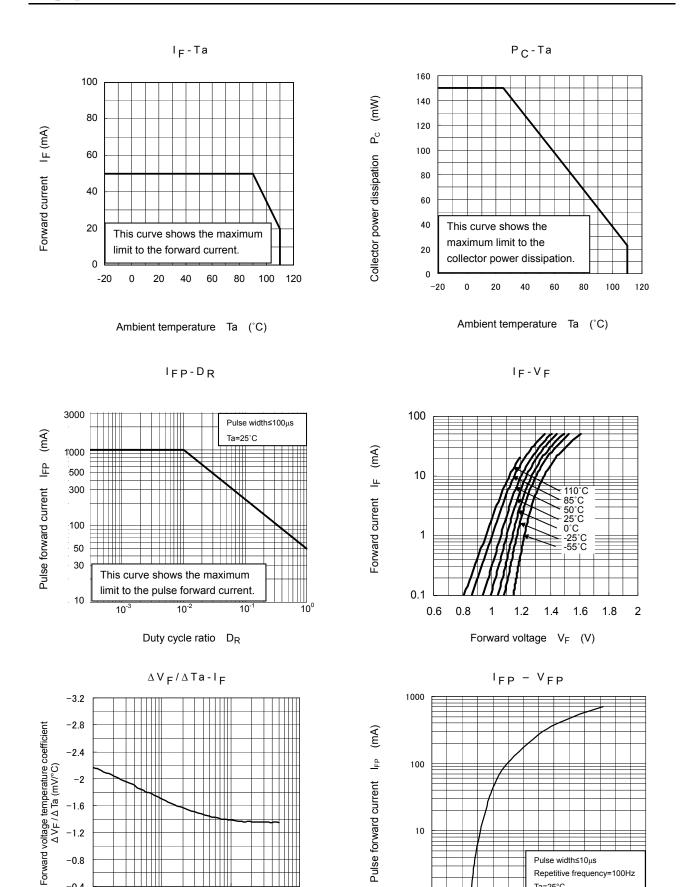
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Rise time	t <sub>r</sub>		_	5	_	
Fall time	t <sub>f</sub>	V <sub>CC</sub> = 10 V, I <sub>C</sub> = 2 mA	_	9	_	μs
Turn-on time	t <sub>on</sub>	$R_L = 100\Omega$	_	9	_	
Turn-off time	t <sub>off</sub>		_	9	_	
Turn-on time	t <sub>on</sub>		_	2	_	
Storage time	t <sub>S</sub>	$R_L = 1.9 \text{ k}\Omega$ (Fig.1) $V_{CC} = 5 \text{ V}, I_F = 16 \text{ mA}$	_	30	_	μS
Turn-off time	t <sub>off</sub>	7 1	_	70	_	

Fig. 1 Switching time test circuit





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Forward current I<sub>F</sub> (mA)

100

-0.8

-0.4

0.1

1.4

0.6

Pulse width≤10μs Repetitive frequency=100Hz

3.4

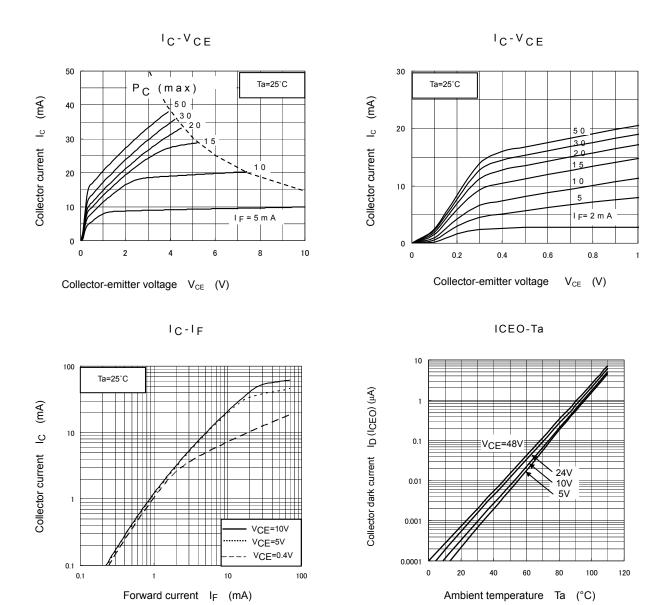
Ta=25°C

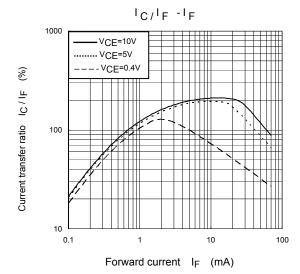
2.2

1.8

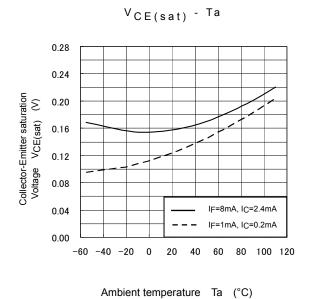
Pulse forward voltage V<sub>FP</sub>

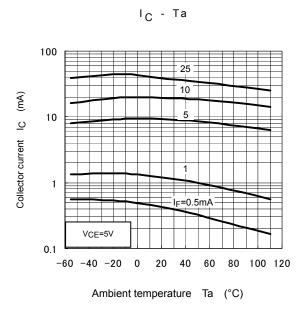
<sup>\*</sup>The above graphs show typical characteristic.

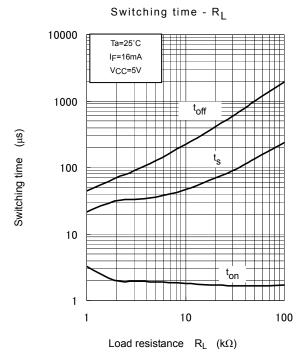


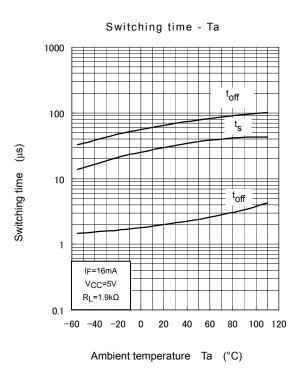


<sup>\*</sup>The above graphs show typical characteristic.









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<sup>\*</sup>The above graphs show typical characteristic.

# **Soldering and Storage**

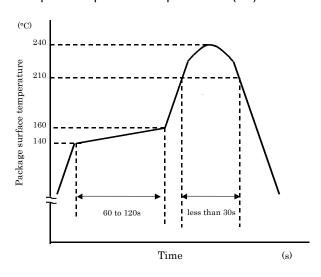
### 1. Soldering

#### 1.1 Soldering

When using a soldering iron or medium infrared ray/hot air reflow, avoid a rise in device temperature as much as possible by observing the following conditions.

#### 1) Using solder reflow

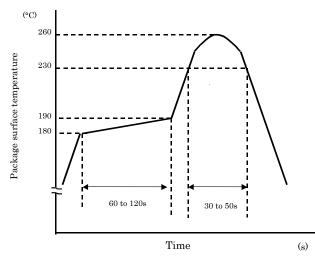
·Temperature profile example of lead (Pb) solder



This profile is based on the device's maximum heat resistance guaranteed value.

Set the preheat temperature/heating temperature to the optimum temperature corresponding to the solder paste type used by the customer within the described profile.

·Temperature profile example of using lead (Pb)-free solder



This profile is based on the device's maximum heat resistance guaranteed value.

Set the preheat temperature/heating temperature to the optimum temperature corresponding to the solder paste type used by the customer within the described profile.

2) Using solder flow (for lead (Pb) solder, or lead (Pb)-free solder)

Please preheat it at 150°C between 60 and 120 seconds.

Complete soldering within 10 seconds below 260°C. Each pin may be heated at most once.

3) Using a soldering iron

Complete soldering within 10 seconds below 260°C, or within 3 seconds at 350°C. Each pin may be heated at most once.

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## 2. Storage

- 1) Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- 2) Follow the precautions printed on the packing label of the device for transportation and storage.
- 3) Keep the storage location temperature and humidity within a range of 5°C to 35°C and 45% to 75%, respectively.
- 4) Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- 5) Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- 6) When restoring devices after removal from their packing, use anti-static containers.
- 7) Do not allow loads to be applied directly to devices while they are in storage.
- 8) If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

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